

What is claimed is:

1. A semiconductor light-emitting element comprising:
a substrate,
a first epitaxial layer group to emit a yellow color light which is provided on the substrate and made of II-VI semiconductor compounds, and
a second epitaxial layer group to emit a blue color light which is provided on the substrate and made of II-VI semiconductor compounds.
2. A semiconductor light-emitting element as defined in claim 1, wherein the first epitaxial layer group includes a light-emitting active layer made of a II-VI semiconductor compound containing Zn, Se, Te and Cd.
3. A semiconductor light-emitting element as defined in claim 2, wherein the light-emitting active layer is made of a II-VI semiconductor compound having a composition of $\text{Zn}_{1-x}\text{Cd}_x\text{Se}_{1-y}\text{Te}_y$ ($0 < x < 0.4$, $0 < y < 0.4$).
4. A semiconductor light-emitting element as defined in claim 2, wherein the first epitaxial layer group includes a first optical waveguide layer and a second optical waveguide layer which are provided so as to sandwich the light-emitting active layer and made of II-VI semiconductor compounds containing Be and Mg, respectively.
5. A semiconductor light-emitting element as defined in claim 4, wherein the first epitaxial layer group includes a first cladding layer and a second cladding layer which are provided so as to sandwich the first optical waveguide layer and the second optical waveguide layer in the outside of the first and the second optical waveguide layers, and made of II-VI semiconductor compounds containing Be and Mg, respectively.
6. A semiconductor light-emitting element as defined in claim 1, wherein the second epitaxial layer group includes a light-emitting active layer made of a II-VI semiconductor compound containing Zn, Se, Te and Cd.
7. A semiconductor light-emitting element as defined in claim 6, wherein the light-emitting active layer is made of a II-VI semiconductor compound having a composition of $\text{Zn}_{1-z}\text{Cd}_z\text{Se}_{1-v}\text{Te}_v$ ($0 < z < 0.1$, $0 < v < 0.1$).
8. A semiconductor light-emitting element as defined in claim 6, wherein the second epitaxial layer group includes a first optical waveguide layer and a second optical waveguide layer which are provided so as to sandwich the light-

emitting active layer and made of II-VI semiconductor compounds containing Be and Mg, respectively.

9. A semiconductor light-emitting element as defined in claim 8, wherein the second epitaxial layer group includes a first cladding layer and a second cladding layer which are provided so as to sandwich the first optical waveguide layer and the second optical waveguide layer in the outside of the first and the second optical waveguide layers, and made of II-VI semiconductor compounds containing Be and Mg, respectively.